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January 2010

# FDS6692A N-Channel PowerTrench<sup>®</sup> MOSFET 30V, 9A, 11.5m $\Omega$

# **Features**

- $R_{DS(ON)} = 11.5 \text{m}\Omega$ ,  $V_{GS} = 10 \text{V}$ ,  $I_D = 9 \text{A}$
- $R_{DS(ON)} = 14.5 \text{m}\Omega$ ,  $V_{GS} = 4.5 \text{V}$ ,  $I_D = 8.2 \text{A}$
- $\blacksquare$  High performance trench technology for extremely low  $R_{\text{DS}(\text{ON})}$
- Low gate charge
- High power and current handling capability
- RoHS Compliant

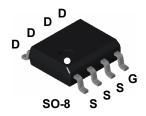
# **Applications**

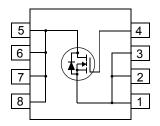
■ DC/DC converters

# **General Description**

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low  $\rm R_{DS(ON)}$  and fast switching speed.







# **MOSFET Maximum Ratings** $T_A = 25$ °C unless otherwise noted

| Symbol                            | Parameter  | Ratings    | Units |
|-----------------------------------|--|------------|-------|
| V <sub>DSS</sub>                  | Drain to Source Voltage  | 30         | V     |
| V <sub>GS</sub>                   | Gate to Source Voltage   | ±20        | V     |
|                                   | Drain Current  |            |       |
| l.                                | Continuous ( $T_A = 25^{\circ}$ C, $V_{GS} = 10$ V, $R_{\theta JA} = 85^{\circ}$ C/W)  | 9          | Α     |
| ΙD                                | Continuous ( $T_A = 25^{\circ}$ C, $V_{GS} = 4.5$ V, $R_{\theta JA} = 85^{\circ}$ C/W) | 8.2        | Α     |
|                                   | Pulsed   | 48         | Α     |
| E <sub>AS</sub>                   | Single Pulse Avalanche Energy (Note 1)   | 79         | mJ    |
| $P_{D}$                           | Power dissipation  | 1.47       | W     |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storage Temperature  | -55 to 150 | °C    |

# **Thermal Characteristics**

| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient at 10 seconds (Note 3)   | 50 | °C/W |
|-----------------|--|----|------|
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient at 1000 seconds (Note 3) | 85 | °C/W |

# **Package Marking and Ordering Information**

| Device Marking | Device   | Package | Reel Size | Tape Width | Quantity   |
|----------------|----------|---------|-----------|------------|------------|
| FDS6692A       | FDS6692A | SO-8    | 330mm     | 12mm       | 2500 units |

# **Electrical Characteristics** T<sub>J</sub> = 25°C unless otherwise noted

| Symbol                             | Parameter                           | Test Conditions                          | Min | Тур | Max  | Units |
|------------------------------------|-------------------------------------|--|-----|-----|------|-------|
| Off Chara                          | acteristics                         |  |     |     |      |       |
| B <sub>VDSS</sub>                  | Drain to Source Breakdown Voltage   | $I_D = 250 \mu A, V_{GS} = 0 V$          | 30  | -   | -    | V     |
| $\Delta B_{VDSS} \over \Delta T_J$ | Breakdown Voltage Temp. Coefficient | $I_D = 250\mu A$ ,<br>Referenced to 25°C | -   | 21  | -    | mV/°C |
| 1                                  | Zero Gate Voltage Drain Current     | V <sub>DS</sub> = 24V                    | -   | -   | 1    | μА    |
| IDSS                               | Zero Gate Voltage Drain Current     | $V_{GS} = 0V$ $T_J = 150^{\circ}C$       | -   | -   | 250  | μΑ    |
| I <sub>GSS</sub>                   | Gate to Source Leakage Current      | V <sub>GS</sub> = ±20V                   | -   | -   | ±100 | nA    |

# On Characteristics

| V <sub>GS(TH)</sub>                 | Gate to Source Threshold Voltage                            | $V_{GS} = V_{DS}, I_D = 250 \mu A$                | 1.2 | -   | 2.5  | V     |
|-------------------------------------|---|---|-----|-----|------|-------|
| $\Delta V_{GS(TH)}$<br>$\Delta T_J$ | Gate to Source Threshold Voltage<br>Temperature Coefficient | I <sub>D</sub> = 250μA,<br>Referenced to 25°C     | -   | -5  | -    | mV/°C |
| R <sub>DS(ON)</sub> Drain to        |   | $I_D = 9A, V_{GS} = 10V$                          | -   | 8.2 | 11.5 |       |
|                                     | Drain to Source On Resistance                               | $I_D = 8.2A, V_{GS} = 4.5V$                       | -   | 11  | 14.5 | mΩ    |
|                                     | Diam to Source Off Hesistance                               | $I_D = 9A, V_{GS} = 10V,$<br>$T_J = 150^{\circ}C$ | -   | 13  | 19   | 11152 |

# **Dynamic Characteristics**

| C <sub>ISS</sub> | Input Capacitance                | 151/1/ 01/   |                       | - | 1210 | 1610 | pF |
|------------------|----------------------------------|--|-----------------------|---|------|------|----|
| C <sub>OSS</sub> | Output Capacitance               | V <sub>DS</sub> = 15V, V <sub>GS</sub> =<br>f = 1MHz | = UV,                 | - | 330  | 440  | pF |
| C <sub>RSS</sub> | Reverse Transfer Capacitance     | 1 - 11/11/2  |                       | - | 138  | 210  | pF |
| $R_G$            | Gate Resistance                  | f = 1MHz   |                       | - | 2.0  | -    | Ω  |
| $Q_{g(TOT)}$     | Total Gate Charge at 10V         | $V_{GS} = 0V \text{ to } 10V$                        |                       | - | 22   | 29   | nC |
| $Q_{g(5)}$       | Total Gate Charge at 5V          | $V_{GS} = 0V \text{ to } 5V$                         | $V_{DD} = 15V$        | - | 12   | 16   | nC |
| $Q_{g(TH)}$      | Threshold Gate Charge            | $V_{GS} = 0V \text{ to } 1V$                         | $I_D = 9A$            | - | 0.93 | 1.2  | nC |
| $Q_{gs}$         | Gate to Source Gate Charge       |  | $I_g = 1.0 \text{mA}$ | - | 3    | -    | nC |
| Q <sub>gs2</sub> | Gate Charge Threshold to Plateau |  |                       | - | 2.1  | -    | nC |
| $Q_{gd}$         | Gate to Drain "Miller" Charge    |  |                       | - | 4.8  | -    | nC |

# Switching Characteristics (V<sub>GS</sub> = 10V)

| t <sub>ON</sub>     | Turn-On Time        |  | - | -  | 60 | ns |
|---------------------|---------------------|--|---|----|----|----|
| t <sub>d(ON)</sub>  | Turn-On Delay Time  |  | ı | 8  | -  | ns |
| t <sub>r</sub>      | Rise Time           | V <sub>DD</sub> = 15V, I <sub>D</sub> = 9A | - | 32 | -  | ns |
| t <sub>d(OFF)</sub> | Turn-Off Delay Time | $V_{GS} = 10V, R_{GS} = 6.2\Omega$         | - | 33 | -  | ns |
| t <sub>f</sub>      | Fall Time           |  | - | 13 | -  | ns |
| t <sub>OFF</sub>    | Turn-Off Time       |  | ı | -  | 69 | ns |

### **Drain-Source Diode Characteristics**

| V <sub>SD</sub> Source to Drain Diode Voltage | Source to Drain Diede Voltage | I <sub>SD</sub> = 9A                    | - | - | 1.25 | V  |
|---|-------------------------------|---|---|---|------|----|
|   | Source to Drain blode Voltage | I <sub>SD</sub> = 2.1A                  | - | - | 1.0  | V  |
| t <sub>rr</sub>                               | Reverse Recovery Time         | $I_{SD} = 9A$ , $dI_{SD}/dt=100A/\mu s$ | - | - | 27   | ns |
| Q <sub>RR</sub>                               | Reverse Recovered Charge      | $I_{SD} = 9A$ , $dI_{SD}/dt=100A/\mu s$ | - | - | 17   | nC |

#### Notes:

Starting T<sub>J</sub> = 25°C, L = 0.3mH, I<sub>AS</sub> = 23A, V<sub>DD</sub> = 27V, V<sub>GS</sub> = 10V.
 R<sub>θ,JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>θ,JC</sub> is guaranteed by design while R<sub>θ,JA</sub> is determined by the user's board design.
 R<sub>θ,JA</sub> is measured with 1.0 in<sup>2</sup> copper on FR-4 board

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# Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

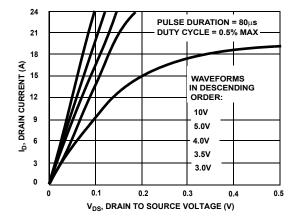


Figure 1. On Region Characteristics

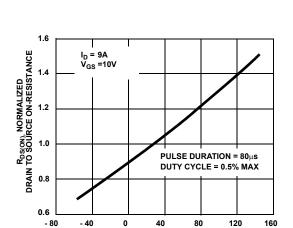


Figure 3. On Resistance Variation with Temperature

T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

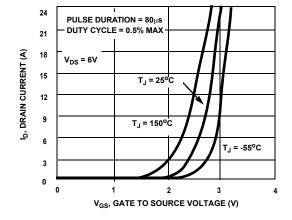


Figure 5. Transfer Characteristics

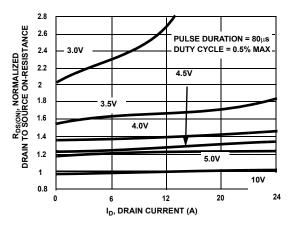


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

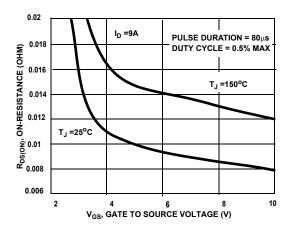


Figure 4. On-Resistance Variation with Gate-to-Source Voltage

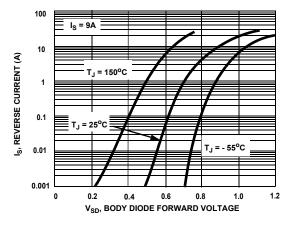
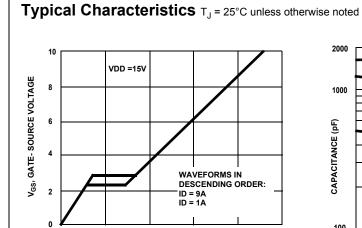
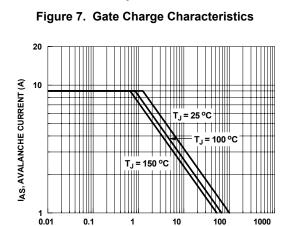


Figure 6. Body Diode Forward Voltage Variation With Source Current and Temperature





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Q<sub>g</sub>, GATE CHARGE (nC)

Figure 9. Unclamped Inductive Switching Capability

t<sub>AV</sub>, TIME IN AVALANCHE (ms)

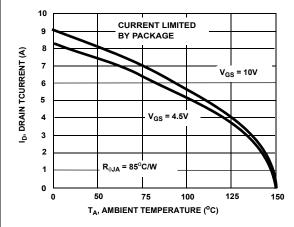


Figure 11. Maximum Continuous Drain Current vs
Ambient Temperature

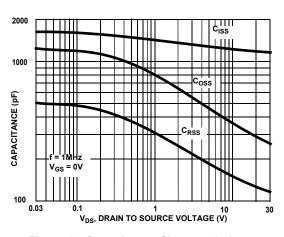


Figure 8. Capacitance Characteristics

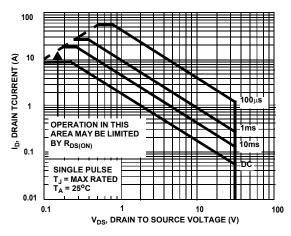


Figure 10. Safe Operating Area

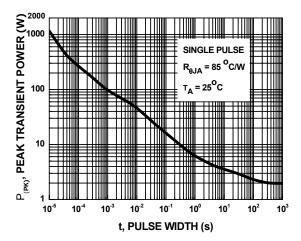


Figure 12. Single Maximum Power Dissipation

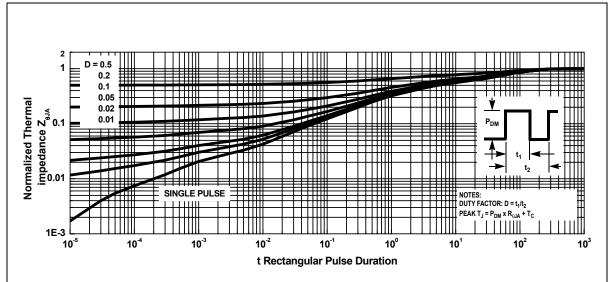


Figure 13. Transient Thermal Response Curve





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